

DOCKET NO.: CACS-0017

A1

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Williams, et al.

Confirmation No.: **6295**

Serial No.: **09/786,176**

Group Art Unit: **2856**

Filing Date: **November 13, 2001**

Examiner: **Politzer, Jay L.**

For: **SEMICONDUCTOR GAS SENSING**

APPENDIX A TO APPLICANTS' BRIEF

- 1) A method of sensing the concentration of O_3 in a gas mixture using a semiconductor gas sensor having a resistivity sensitive to O_3 , which comprises increasing the sensor operating temperature to a first temperature to allow the sensor surface to reset then decreasing the sensor operating temperature to a second temperature and analyzing the resultant resistance of the sensor at the second temperature, wherein the sensor is a layer of WO_3 , the first temperature is 400 to 800 °C, the second temperature is 200 to 500 °C, and the first temperature is higher than the second temperature.

- 3) A method according to claim 1 wherein the sensor resistance is analyzed as a function of time.